

## SK510B SCHOTTKY RECTIFIER

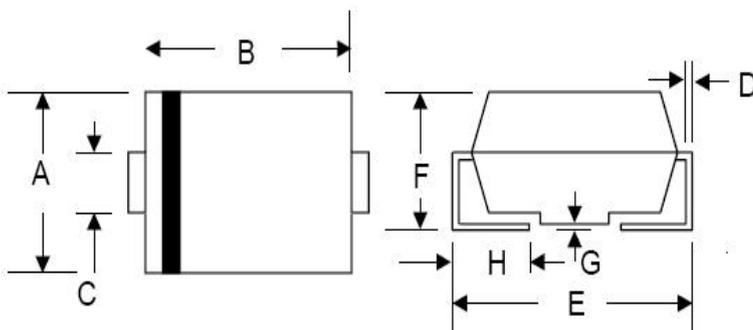
### Applications:

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Disk drives
- Battery charging

### Features:

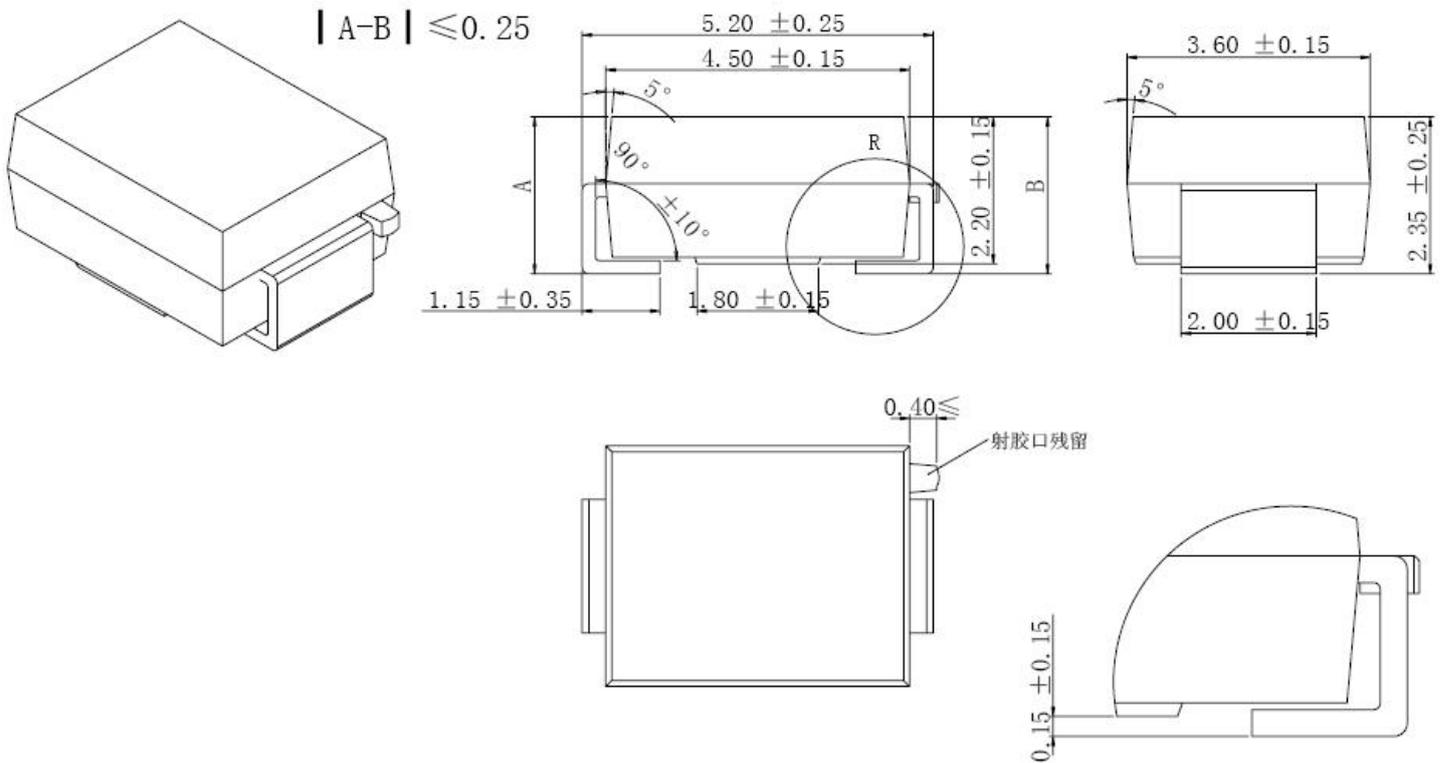
- Small foot print, surface mountable
- Very low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Green products in compliance the ROHS directive
- This is a Pb - Free device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

### Mechanical Dimensions: In mm



SMB/DO-214AA				
Dim	Min	Max	Min	Max
A	3.30	3.94	0.130	0.155
B	4.06	4.70	0.160	0.185
C	1.91	2.11	0.075	0.083
D	0.152	0.305	0.006	0.012
E	5.08	5.59	0.2	0.220
F	2.13	2.44	0.084	0.096
G	0.051	0.203	0.002	0.008
H	0.76	1.27	0.029	0.05
	in mm		In inch	

### OPTION 1



**OPTION 2(JK)**

**SMB**

**Marking Diagram:**



Where XXXXX is YYWWL

SK = Device Type  
5 = Forward Current (5A)  
10 = Reverse Voltage (100V)  
B = Package type  
YY = Year  
WW = Week  
L = Lot Number

**Cautions:** Molding resin  
Epoxy resin UL:94V-0

**Ordering Information:**

Device	Package	Shipping
SK510B	SMB (Pb-Free)	3000pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

**Maximum Ratings:**

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$V_{RRM}$ $V_{RWM}$ $V_R$	-	100	V
Average Rectified Forward Current	$I_{F(AV)}$	50% duty cycle @ $T_L=115^\circ\text{C}$ , rectangular wave form	5	A
Peak one Cycle Non-repetitive Surge Current	$I_{FSM}$	8.3 ms, half Sine pulse	120	A

**Electrical Characteristics:**

Characteristics	Symbol	Condition	Max.	Units
Forward Voltage Drop (per leg) *	V <sub>F1</sub>	@ 5A, Pulse, T <sub>J</sub> = 25 °C	0.85	V
	V <sub>F2</sub>	@ 5 A, Pulse, T <sub>J</sub> = 125 °C	0.70	V
Reverse Current (per leg) *	I <sub>R1</sub>	@V <sub>R</sub> = rated VR T <sub>J</sub> = 25 °C	0.1	mA
	I <sub>R2</sub>	@V <sub>R</sub> = rated VR T <sub>J</sub> = 100 °C	2.0	mA
Junction Capacitance (per leg)	C <sub>T</sub>	@V <sub>R</sub> = 4V, T <sub>C</sub> = 25 °C f <sub>SIG</sub> = 1MHz	200	pF
Voltage Rate of Change	dv/dt	-	10,000	V/us

\* Pulse Width < 300μs, Duty Cycle <2%

**Thermal-Mechanical Specifications:**

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	T <sub>J</sub>	-	-55 to +150	°C
Storage Temperature	T <sub>stg</sub>	-	-55 to +150	°C
Typical Thermal Resistance Junction to Lead	R <sub>θJL</sub>	-	17	°C/W
Typical Thermal Resistance, Junction to Ambient	R <sub>θJA</sub>	-	75	°C/W
Approximate Weight	wt	-	0.68	g
Case Style	SMB			

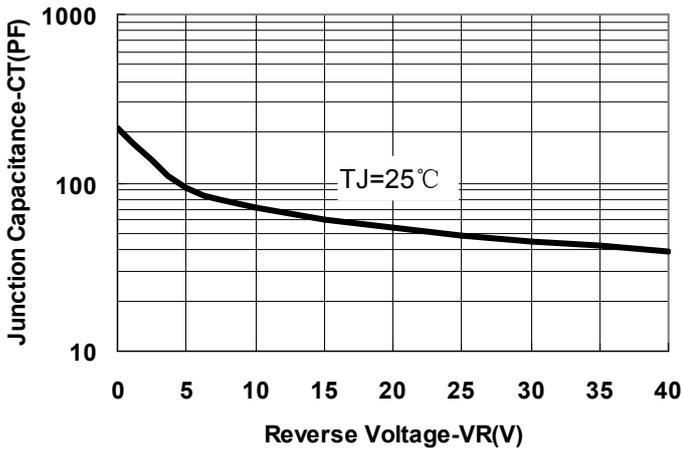


Fig.1-Typical Junction Capacitance Vs. Reverse Voltage

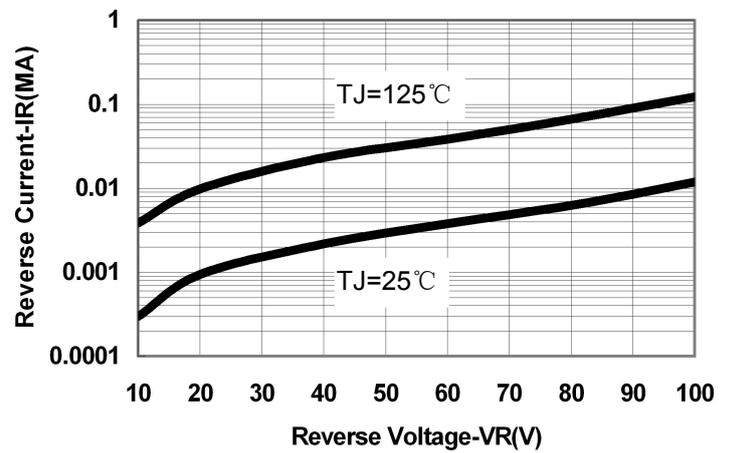


Fig.2-Typical Values Of Reverse Current Vs. Reverse Voltage

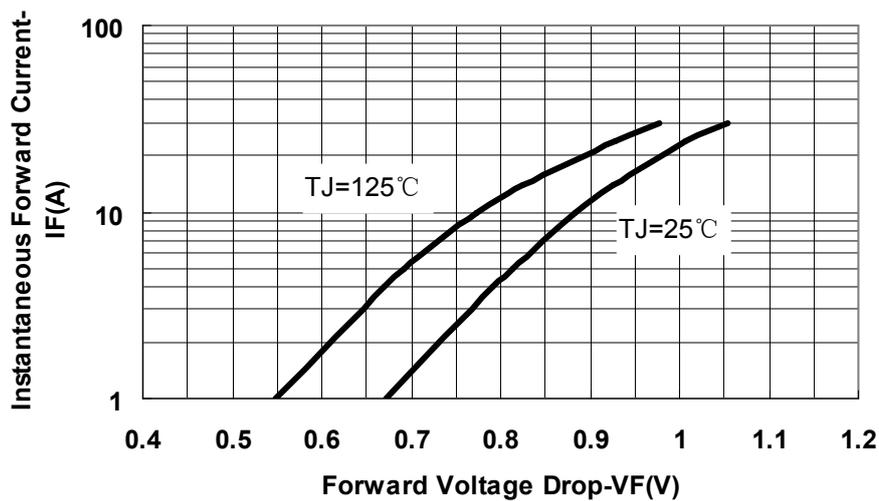


Fig.3-Typical Forward Voltage Drop Characteristics

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